


 Cite this: *RSC Adv.*, 2018, 8, 28692

Correction: A vertical WSe₂–MoSe₂ p–n heterostructure with tunable gate rectification

Hailiang Liu,^{ab} Sajjad Hussain,^{ab} Asif Ali,^{ab} Bilal Abbas Naqvi,^{ab}
Dhanasekaran Vikraman,^c Woonyoung Jeong,^{ab} Wooseok Song,^d Ki-Seok An^d
and Jongwan Jung^{*ab}

DOI: 10.1039/c8ra90067a

www.rsc.org/advances

Correction for 'A vertical WSe₂–MoSe₂ p–n heterostructure with tunable gate rectification' by Hailiang Liu et al., *RSC Adv.*, 2018, 8, 25514–25518.

The authors regret that Hailiang Liu's name was spelled incorrectly in the original article; the corrected version is shown above. The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.



^aGraphene Research Institute, Sejong University, Seoul 143-747, Republic of Korea. E-mail: jwjung@sejong.ac.kr

^bInstitute of Nano and Advanced Materials Engineering, Sejong University, Seoul 143-747, Republic of Korea

^cDivision of Electronics and Electrical Engineering, Dongguk University-Seoul, Seoul 04620, Republic of Korea

^dThin Film Materials Research Center, Korea Research Institute of Chemical Technology, Daejeon 305-600, Korea